Silicon Switching Diode

1N4148 or 1N4148-1

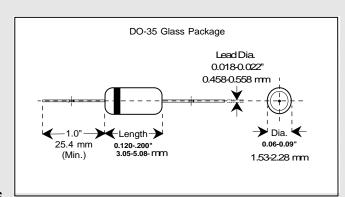
DO-35 Glass Package

Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond[™] plating for problem free solderability
- LL-34/35 MELF SMD available
- Hermetic Glass Body
- Available up to JANTXV-1 levels
- "S" level screening available to Source Control Drawings-



Maximum Ratings			Symbo	ol Value	Unit
Peak Inverse Voltage			PIV	100 (Min).	Volts
Average Rectified Current			lavg	200	mAmps
Continuous Forward Current			 Fdc	300	mAmps
Peak Surge Current (t _{peak} = 1 sec.)			 peak	1.0	Amp
BKC Power Dissipation $T_L=50 \text{ °C}$, L = 3/8" from body			P _{tot}	500	mWatts
Operating Temperature Range			T_{Op}	-65 to +200	° C
Storage Temperature Range		T_{St}	-65 to +200	° C	
Electrical Characteristics @ 25°C*	Symbol	Mi	nimum	Maximum	Unit
Forward Voltage Drop @ I _F = 10 mA	V_{F}	*	***	1.00	Volts
Breakdown Voltage @ I _R = 5 μA	PIV	-	75		Volts
Breakdown Voltage @ I _R =100µA	PIV	1	00		Volts
Reverse Leakage Current @ V _R = 75 V	I _R			5 (100 @ 150 °C)	μΑ
Capacitance @ V _R = 0 V, f = 1mHz	C_{T}			4.0	pF
Reverse Recovery time (note 1)	t _{rr}			4.0	nSecs

Note 1: Per Method 4031-A with $I_F = 10$ mA, Vr = 6 V, $R_L = 100$ Ohms. * UNLESS OTHERWISE SPECIFIED

